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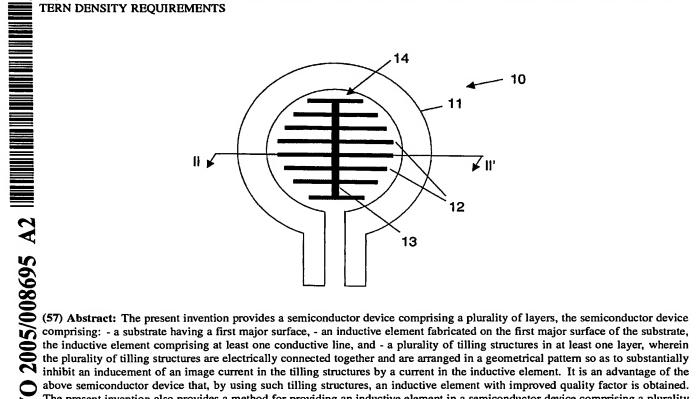
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- (71) Applicant (for all designated States except US): KONIN-KLIJKE PHILIPS ELECTRONICS N.V. [NL/NL]: Groenewoudseweg 1, NL-5621 BA Eindhoven (NL).
- (72) Inventors; and
- (75) Inventors/Applicants (for US only): DETCHEVERRY, Celine, J. [FR/BE]; c/o Prof. Holstlaan 6, NL-5656 AA Eindhoven (NL). VAN NOORT, Wibo, D. [NL/BE]; c/o Prof. Holstlaan 6, NL-5656 AA Eindhoven (NL).

- (74) Agent: ELEVELD, Koop, J.; Prof. Holstlaan 6, NL-5656 AA Eindhoven (NL).
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(54) Title: INDUCTIVE AND CAPACITIVE ELEMENTS FOR SEMICONDUCTOR TECHNOLOGIES WITH MINIMUM PAT-TERN DENSITY REQUIREMENTS



above semiconductor device that, by using such tilling structures, an inductive element with improved quality factor is obtained. The present invention also provides a method for providing an inductive element in a semiconductor device comprising a plurality of layers.

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